July 2005

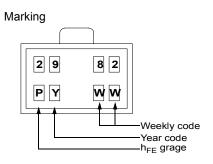
FAIRCHILD SEMICONDUCTOR®

KSC2982 NPN Epitaxial Silicon Transistor

Strobe Flash & Medium Power Amplifier

- Excellent h_{FE} Linearity : h_{FE1}=140 ~ 600
- Low Collector-Emitter Saturation Voltage : V_{CE}(sat)=0.5V
- + Collector Dissipation : $P_C=1\sim 2W$ in Mounted on Ceramic Board





Absolute Maximum Ratings $T_a = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	30	V
V _{CES}	Collector-Emitter Voltage	30	
V _{CEO}	Collector-Emitter Voltage	10	V
V _{EBO}	Emitter Base Voltage	6	V
I _C	Collector Current (DC)	2	A
I _{CP}	Collector Current (Pulse) *	4	A
I _B	Base Current (DC)	0.4	А
I _{BP}	Base Current (Pulse) *	0.8	A
P _C P _C *	Collector Power Dissipation	500 1,000	mW mW
TJ	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

* PW \leq 10ms, Duty Cycle \leq 30%

Mounted on Ceramic Board (250mm² x 0.8mm)

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Electrical Characteristics T_a = 25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA, I _B = 0	10			V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 1mA, I _C = 0	6			V
I _{CBO}	Collector Cut-off Current	V _{CB} = 30V, I _E = 0			100	nA
I _{EBO}	Emitter Cut-off Current	V _{BE} = 6V, I _C = 0			100	nA
h _{FE1} h _{FE2}	DC Current Gain	$V_{CE} = 1V, I_C = 0.5A$ $V_{CE} = 1V, I_C = 2A$	140 70	140	600	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = 2A, I _B = 50mA		0.2	0.5	V
V _{BE} (on)	Base-Emitter On Voltage	V _{CE} = 1V, I _C = 2A		0.86	1.5	V
f _T	Current Gain Bandwidth Product	V _{CE} = 1V, I _C = 2A		150		MHz
C _{ob}	Output Capacitance	V _{CB} = 10V, I _E = 0, f = 1MHz		27		pF

h_{FE} Classification

Classification	Α	В	С	D
h _{FE1}	140 ~ 240	200 ~ 330	300 ~ 450	420 ~ 600

Package Marking and Ordering Information

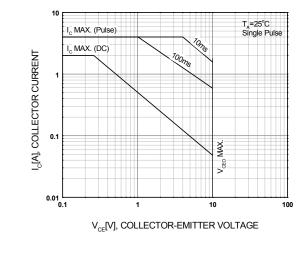
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
2982	KSC2982	SOT-89	13"		4,000

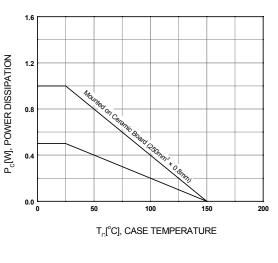
KSC2982 NPN Epitaxial Silicon Transistor

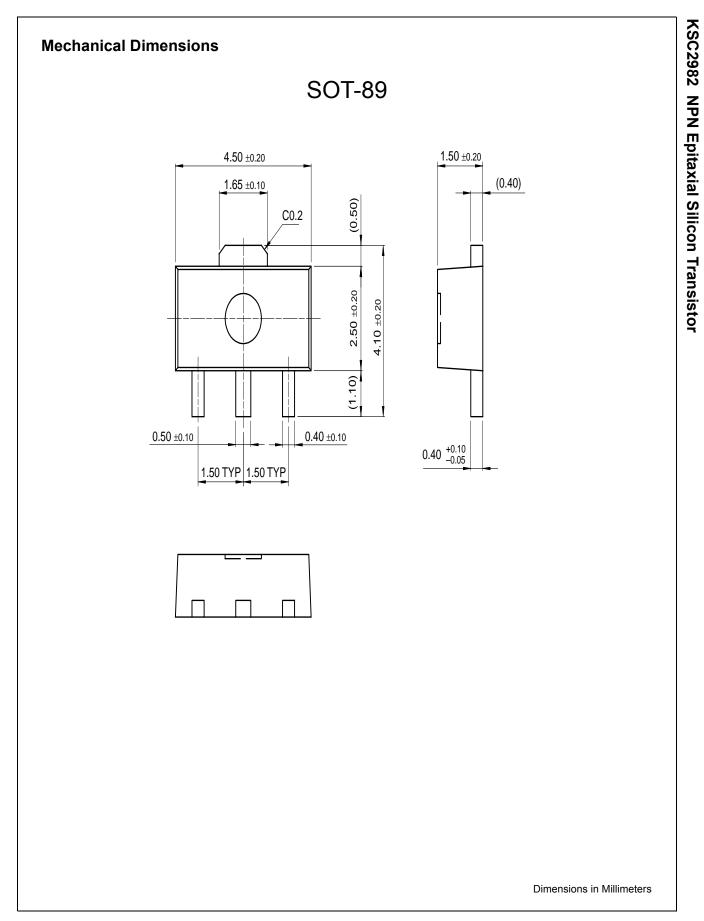
10

200

Typical Performance Characteristics Figure 1. Static Characteristic Figure 2. DC Current Gain = 60mA 1. = 25mA 1,000 V_{CE}=1V I_B = 15mA I_c[A], COLLECTOR CURRENT 3 h_{FE}, DC CURRENT GAIN , = 10mA 2 100 $I_{R} = 5 mA$ $I_{\rm B} = 0 \text{mA}$ 10 L 0.01 0.1 2 3 1 0 V_{CE}[V], COLLECTOR-EMITTER VOLTAGE Ic[A], COLLECTOR CURRENT Figure 3. DCollector-Emitter Saturation Voltage Figure 4. Base-Emitter On Voltage 1.6 I_C=10 I_B V_{CE}(sat)[V], SATURATION VOLTAGE P_c[W], POWER DISSIPATION 1.2 0.1 0.8 0.4 0.01 0.0 L 0 0.1 1 10 50 100 150 Ic[A], COLLECTOR CURRENT T_c[°C], CASE TEMPERATURE Figure 5. Safe Operating Area Figure 6. Power Derating 1.6 10







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FACT™	IntelliMAX™	OPTOLOGIC®	SMART START™	whe
FACT Quiet Series™		OPTOPLANAR™	SPM™	
Across the board. Arour The Power Franchise [®] Programmable Active D		PACMAN™ POP™ Power247™ PowerEdge™	Stealth™ SuperFET™ SuperSOT™-3 SuperSOT™-6	

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Definition of Terms

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